



Heriot-Watt University
Research Gateway

Comment on “Diffusion of n-type dopants in germanium” [Appl. Phys. Rev. 1, 011301 (2014)]

Citation for published version:

Cowern, NEB, Simdyankin, S, Goss, JP, Napolitani, E, De Salvador, D, Bruno, E, Mirabella, S, Ahn, C & Bennett, NS 2015, 'Comment on “Diffusion of n-type dopants in germanium” [Appl. Phys. Rev. 1, 011301 (2014)]', *Applied Physics Reviews*, vol. 2, no. 3, 036101. <https://doi.org/10.1063/1.4929762>

Digital Object Identifier (DOI):

[10.1063/1.4929762](https://doi.org/10.1063/1.4929762)

Link:

[Link to publication record in Heriot-Watt Research Portal](#)

Document Version:

Publisher's PDF, also known as Version of record

Published In:

Applied Physics Reviews

General rights

Copyright for the publications made accessible via Heriot-Watt Research Portal is retained by the author(s) and / or other copyright owners and it is a condition of accessing these publications that users recognise and abide by the legal requirements associated with these rights.

Take down policy

Heriot-Watt University has made every reasonable effort to ensure that the content in Heriot-Watt Research Portal complies with UK legislation. If you believe that the public display of this file breaches copyright please contact open.access@hw.ac.uk providing details, and we will remove access to the work immediately and investigate your claim.

Comment on “Diffusion of n-type dopants in germanium” [Appl. Phys. Rev. 1, 011301 (2014)]

N. E. B. Cowern, S. Simdyankin, J. P. Goss, E. Napolitani, D. De Salvador, E. Bruno, S. Mirabella, C. Ahn, and N. S. Bennett

Citation: [Applied Physics Reviews](#) **2**, 036101 (2015); doi: 10.1063/1.4929762

View online: <http://dx.doi.org/10.1063/1.4929762>

View Table of Contents: <http://scitation.aip.org/content/aip/journal/apr2/2/3?ver=pdfcov>

Published by the [AIP Publishing](#)

Articles you may be interested in

[Response to “Comment on ‘Diffusion of n-type dopants in germanium’” \[Appl. Phys. Rev. 2, 036101 \(2015\)\]](#)
Appl. Phys. Rev. **2**, 036102 (2015); 10.1063/1.4929763

[Diffusion of n-type dopants in germanium](#)
Appl. Phys. Rev. **1**, 011301 (2014); 10.1063/1.4838215

[Interaction of n-type dopants with oxygen in silicon and germanium](#)
J. Appl. Phys. **112**, 073706 (2012); 10.1063/1.4757406

[Multiple implantation and multiple annealing of phosphorus doped germanium to achieve n-type activation near the theoretical limit](#)
Appl. Phys. Lett. **101**, 112107 (2012); 10.1063/1.4751845

[On the diffusion and activation of ion-implanted n-type dopants in germanium](#)
J. Appl. Phys. **106**, 103516 (2009); 10.1063/1.3261838



AIP | Journal of
Applied Physics

Journal of Applied Physics is pleased to
announce **André Anders** as its new Editor-in-Chief

APPLIED PHYSICS REVIEWS

Comment on “Diffusion of n-type dopants in germanium” [Appl. Phys. Rev. 1, 011301 (2014)]

N. E. B. Cowern,^{1,a)} S. Simdyankin,¹ J. P. Goss,¹ E. Napolitani,² D. De Salvador,² E. Bruno,³ S. Mirabella,³ C. Ahn,⁴ and N. S. Bennett⁵

¹School of Electrical and Electronic Engineering, Newcastle University, Newcastle upon Tyne NE1 7RU, United Kingdom

²CNR-IMM-MATIS and Dipartimento di Fisica, Università di Padova, Via Marzolo 8, 35131 Padova, Italy

³CNR-IMM-MATIS and Dipartimento di Fisica e Astronomia, Università di Catania, Via S. Sofia 64, 95123 Catania, Italy

⁴Samsung Semiconductor, Inc., 3655 North First Street, San Jose, California 95134, USA

⁵Institute of Mechanical, Process and Energy Engineering, School of Engineering and Physical Sciences, Heriot-Watt University, Edinburgh EH14 4AS, United Kingdom

(Received 11 June 2014; accepted 26 June 2015; published online 2 September 2015)

The authors of the above paper call into question recent evidence on the properties of self-interstitials, I, in Ge [Cowern *et al.*, Phys. Rev. Lett. **110**, 155501 (2013)]. We show that this judgment stems from invalid model assumptions during analysis of data on B marker-layer diffusion during proton irradiation, and that a corrected analysis fully supports the reported evidence. As previously stated, I-mediated self-diffusion in Ge exhibits two distinct regimes of temperature, T : high- T , dominated by amorphous-like mono-interstitial clusters—i-morphs—with self-diffusion entropy $\approx 30k$, and low- T , where transport is dominated by simple self-interstitials. In a transitional range centered on 475 °C both mechanisms contribute. The experimental I migration energy of 1.84 ± 0.26 eV reported by the Münster group based on measurements of self-diffusion during irradiation at $550^\circ\text{C} < T < 680^\circ\text{C}$ further establishes our proposed i-morph mechanism. © 2015 AIP Publishing LLC. [<http://dx.doi.org/10.1063/1.4929762>]

A recent *Applied Physics Review* has discussed self-diffusion and B diffusion during irradiation at high temperature.¹ Unfortunately, erroneous assumptions in B diffusion data analysis led the authors mistakenly to critique recent work by us that identified two forms of self-interstitial in Ge.² Here, we show that their work when correctly interpreted confirms our conclusions. In the following discussion, C_X and D_X represent the concentration and diffusivity of species X, E_f^X and E_m^X (S_f^X and S_m^X) its formation and migration energies (entropies), respectively, and $D_{SD}^X = D_X C_X^{eq}/C_0$, where C_0 is the lattice density, is the contribution of X to equilibrium self-diffusion with activation energy E_{SD}^X and activation entropy S_{SD}^X . The species described are the vacancy, V, self-interstitial, I, and B-interstitial pair, BI, and we consider two distinct forms of I; I and \mathcal{I} . The first is the compact I, well known from the literature, the second is the *i-morph*—an extended self-interstitial with properties of a small amorphous pocket.² This entity, in some ways reminiscent of the high-temperature “liquid drop” proposed by Seeger,^{3,4} however, needs to be understood from a fundamentally different perspective; the key feature is an *amorphous*-like property with corresponding energetic and entropic behavior.²

Our evidence has been disputed by Bracht and co-workers.^{1,5} Their objection appears to be based on (a) a misunderstanding of our analysis of long-range BI migration in Ref. 2, (b) an erroneous analysis of BI mediated B diffusion in Ref. 1 and a precursor paper.⁶ To clarify the issues, we first briefly review the disputed analysis of Ref. 2. B diffuses in Ge, as in Si,⁷ via a fast migrating BI pair formed by the reaction $B_s + I \leftrightarrow BI$.⁸ A parallel reaction, $B_s \leftrightarrow BI + V$, also occurs but has no significant influence under the conditions of Refs. 1 and 2. BI in Ge, as in Si, has a large migration length, λ —a quantity closely connected to the difference in Gibbs free energy between BI and I.² This leads to exponential diffusion tails after anneal times short enough that only a fraction of C_{B_s} experiences a reaction with I to form BI. This behavior occurs under both equilibrium and irradiation conditions, with λ independent of I supersaturation.^{7,8}

To analyse this behavior, the diffusion of I, BI, and V can be modeled by numerical solution of the coupled equation system as in Refs. 1 and 6 and elsewhere. Under certain conditions, the full system can be reduced to one equation which has an analytical solution involving just g , λ , position, and time—the g - λ solution.^{7,9} This is a mathematical approximation to the full equation system that describes the detailed properties of dopant diffusion and is applicable under equilibrium and non-equilibrium conditions. The necessary and sufficient conditions for accuracy of this approximation are

^{a)}Electronic mail: nick.cowern@ncl.ac.uk

that $C_{BI} \ll C_{Bs}$, the Fermi level at the diffusion temperature, T , is slowly varying in the local region of interest, and there are no significant gradients in C_I or C_V . The latter condition prevails if $D_B C_B \ll D_I C_I^{eq}$, and no significant gradients are generated by external processes. It is *not* necessary to assume point-defect equilibrium. When the preceding inequality is relaxed towards $D_B C_B \sim D_I C_I^{eq}$, the rate of the reaction $I + B_s \rightarrow BI$ is slightly modified by “chemical pump” effects but the g - λ solution still accurately describes λ .¹⁰

In the experiments of Ref. 2, all these conditions were satisfied, so the g - λ approach could be used to extract accurate λ values from our experimental secondary-ion mass spectrometry (SIMS) profiles, thus avoiding the costly use of a general diffusion solver as kernel in least-squares minimization. Following this analysis, we deduced a T -dependent free-energy difference between BI and I, indicating that the latter has two distinct forms. The first, dominating I-mediated transport at low T , is the simple I. The second, dominating D_{SD}^I at high T , is an extended I; the *i*-morph.² A transitional region, where both defect forms contribute, exists over a $\sim 100^\circ\text{C}$ range centered on 475°C . Reference 1 cites this analysis, claiming in error that the g/λ approach is inapplicable under non-equilibrium conditions.

We now consider the analysis of B diffusion in Refs. 1 and 6. Fig. 17 of Ref. 1 presents B profiles in Ge measured by SIMS after proton irradiation of a B-doped Ge superlattice at 550 and 630°C . To show clearly the detailed B profile shape evolution during diffusion, we have selected and plotted the data for a single marker layer in Fig. 1. The profile shows characteristic exponential-like tails (showing up as almost straight lines on the logarithmic plot of Fig. 1) on each side of the B-doped marker layers. The curves turn up at the edges of the plot owing to overlap of diffusion from neighboring markers. The data at 550°C show significantly more diffusion than at 630°C , because at lower T both λ ($= \{D_{BI}/(k_1^+ C_0)\}^{1/2}$ in Bracht’s notation) and the forward reaction rate g ($= k_1^- C_I$) are larger. The larger λ reflects the increased number of BI diffusion jumps per migration event as the thermal energy available for dissociation, $BI \rightarrow B + I$, is reduced. The larger g reflects the increased number of lattice sites each beam-generated I visits before recombining with V. The static peak represents those B_s which have not yet undergone reaction (1)—a statistical effect due to the finite arrival rate of I at B_s .

The approach taken in Ref. 1, following Ref. 6, fails to recognize and model these key effects. This seems to be caused by unrealistic assumptions (a) on B clustering during annealing of initially substitutional B, (b) that $C_{BI} \gg C_{Bs}$. In relation to point (a), Ref. 6 assumed *a priori* that, at all considered anneal times, t , each B marker had a large clustered component, adjusted for each T/t combination to keep $C_{Bs} \leq 5 \times 10^{18} \text{cm}^{-2}$. This ignores the transient dynamics of B clustering in the MBE-grown doping structure as BI migrates and traps on other B atoms. In the simulations of Ref. 6 (Fig. 17), clustering, unrealistically, actually *decreases* with time. Point (b) is a result of assuming $S_f^{BI} \approx 30k$ —a problematic choice as the entropy of D_B , $S_f^{BI} + S_m^{BI} \approx 20k$ ¹¹ and negative S_m^{BI} is highly unlikely. It is unclear why such a large S_f^{BI} has been used, unless it is to prevent D_B from

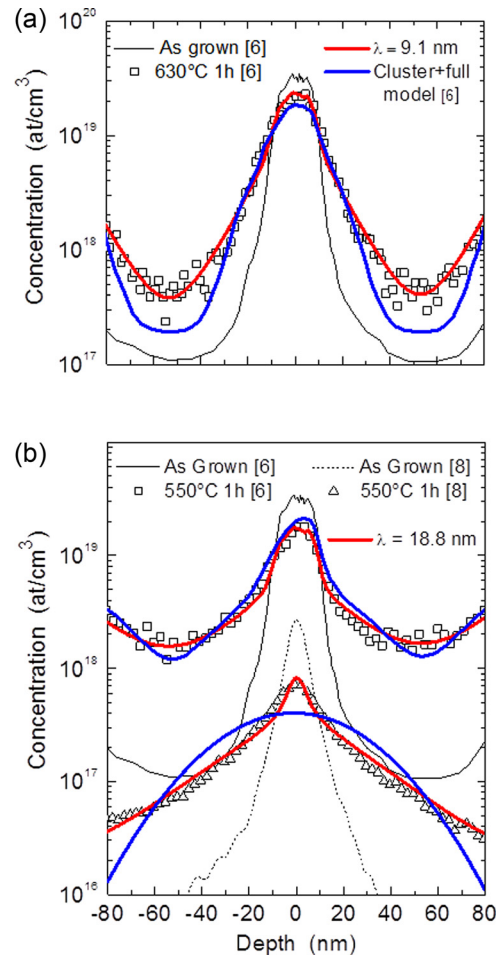


FIG. 1. Fits to data discussed in Refs. 1 and 2 using the method of Ref. 2 (red curves). The high quality of fit assures that extracted values of λ (18.8 nm at $T = 550^\circ\text{C}$ and 9.1 nm at $T = 630^\circ\text{C}$) are close to the true migration length of BI at each T . Exponential tails indicate intermittent diffusion via fast-migrating BI with $C_{BI} \ll C_{Bs}$.^{7,8} Simulations assuming $C_{BI} \gg C_{Bs}$ (blue curves) give poor fits as this choice implies that all non-clustered B atoms diffuse continuously, leading to Gaussian curves at low B concentration (see especially the bottom blue curve).

varying as $(p/n_i)^2$ as the model assumes BI is in a singly positive charge state.⁶ The result of these several choices is that all the simulated profiles have Gaussian shapes at low B concentration (blue curves in Fig. 1). This is a poor fit to the data, which show a clear exponential-like trend, thus directly demonstrating that $C_{BI} \ll C_{Bs}$, refuting assumption (b) above and rendering equation (20) and Fig. 6 of Ref. 6 invalid. This key point is further underscored by the fact that proton irradiation experiments with almost identical Frenkel-pair production rates¹² to those used in Ref. 1 explicitly show $g \propto \phi$, where ϕ is the beam flux⁸ (a test not reported in Refs. 1 and 6). The failure of the assumption $C_{BI} \gg C_{Bs}$ is most graphically evident in the lower panel in Fig. 1, where we present data from an earlier study⁸ using very similar processing conditions. The data show essentially the same exponential tails as in Ref. 1, although in this case clustering is entirely absent, all B is available to diffuse, and the static peak represents those B atoms which have escaped interaction with I during the short annealing time. The imposition of $C_{BI} \gg C_{Bs}$, however, identifies essentially all unclustered B as continuously diffusing BI, leading to a Gaussian diffusion profile.

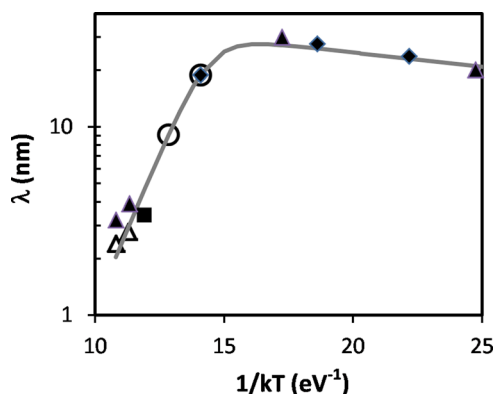


FIG. 2. Migration length of BI in Ge versus $1/kT$. Solid symbols: data from proton irradiation experiments using low peak B concentration to ensure ideal conditions for extracting λ .² Open circles: values from Fig. 1 (both low and high peak B concentrations). Open triangle: value obtained after furnace annealing in inert ambient.^{14,15} The curve is the fit reported in Ref. 2 based on two forms of self-interstitial in Ge. The data from Ref. 1 are clearly consistent with our modeling and conclusions.

Fully coupled models as in Refs. 1 and 6 easily reproduce observed exponential tails if model parameters are correct. A first step towards this goal is to eliminate the unrealistic saturation of C_{BI} . This can be done by reducing S_f^{BI} from $30k$ to below $20k$. This then allows extraction of other key parameters, inaccessible with the assumption $C_{BI} \gg C_{BS}$, such as the charge states of BI and I (from data on the Fermi-level dependence of B diffusion), and E_f^I , S_f^I (from exponential tails, since E_f^I , S_f^I determine the parameter k_1^+ in $\lambda = \{D_{BI}/(k_1^+ C_0)\}^{1/2}$ (Refs. 2 and 6)).

In Refs. 1 and 6, the peak C_B is $\sim 10\times$ higher than in earlier experiments.² In this situation, clustering, chemical-pump, and Fermi-level effects may all influence diffusion, so the data in Ref. 1 are a more complex resource for parameter determination than those in Ref. 2. Nevertheless, to illustrate the robustness of λ extraction with the g - λ approximation, we apply it, outside its strictly applicable range, to the “short-time” (1 h) B data of Refs. 1 and 6. The results, using the same λ values as in Ref. 2, are shown in Fig. 1 (red curves).¹³ The fits are essentially perfect—far better than those obtained in Refs. 1 and 6. Moreover, unlike the fits in Ref. 1 they respect the data from Ref. 8, which explicitly showed $C_{BI} \ll C_{BS}$. It should now be clear that our analysis in Ref. 2, where conditions were optimal for λ extraction, is extremely robust. Moreover, the B data discussed in Ref. 1 support the analysis in Ref. 2, not refuting it as claimed.¹ The B model parameters used in Ref. 1, however, are far from correct. We now restate the established position:² our data (further supported by high- T data in Refs. 1 and 6) show that I-mediated self-diffusion in Ge involves a simple I at low T (significantly below 475°C), an i-morph, \mathcal{I} , with $S_{SD}^{\mathcal{I}} \approx 30k$, $E_{SD}^{\mathcal{I}} \approx 6.1\text{ eV}$ at high T (significantly above 475°C), and a transitional region around 475°C where both are significant. Finally, it should be noted that the open triangle^{14,15} in Fig. 2 shows that B also diffuses via BI under equilibrium conditions. An alternative model based on vacancy exchange¹ would imply jump lengths of only 0.25 nm .

Having dealt with B diffusion analysis in some detail in this comment, we would like to emphasize that Section V of Ref. 1 also references an elegant analysis of experiments by the Munster group and coworkers on the diffusivity of I in irradiation experiments on Ge isotope superlattices.⁶ That analysis revealed $E_m^I = (1.84 \pm 0.26)\text{ eV}$. This value far exceeds estimates of $0.5\text{--}0.6\text{ eV}$ obtained from perturbed angular correlation measurements at low T ,^{16,17} 0.6 eV obtained for simple I configurations from density functional theory using accurate LDA + U functionals,¹⁸ and $<1\text{ eV}$ indicated by jump rates exceeding $\sim 1\text{ s}^{-1}$ at RT for I directly observed in aberration-corrected TEM.¹⁹ Thus in retrospect one can see that the 1.84 eV value rules out the simple I assumed in Ref. 1 and strongly favors the i-morph mechanism we proposed in Ref. 2. This has vast implications for defect physics which remain to be explored. Finally, taken together with our observed $E_{SD}^{\mathcal{I}} = 6.1\text{ eV}$ at high T ,² $E_m^{\mathcal{I}} = 1.84\text{ eV}$ implies $E_f^{\mathcal{I}} \approx 4.3\text{ eV}$, in the range of recent atomistic calculations in course of publication.²⁰ In conclusion, discussion prompted by conflicting analyses of experiments in Refs. 1, 2, and 6 has significantly progressed understanding of the complex behavior of self-interstitials in Ge.

¹A. Chroneos and H. Bracht, *Appl. Phys. Rev.* **1**, 011301 (2014).

²N. E. B. Cowern, S. Simdyankin, C. Ahn, N. S. Bennett, J. P. Goss, J.-M. Hartmann, A. Pakfar, S. Hamm, J. Valentin, E. Napolitani, D. De Salvador, E. Bruno, and S. Mirabella, *Phys. Rev. Lett.* **110**, 155501 (2013).

³A. Seeger and K. P. Chik, *Phys. Status Solidi* **29**, 455 (1968).

⁴A. Seeger, *Phys. Status Solidi B* **248**, 2772 (2011).

⁵H. Bracht, R. Kube, E. Hüger, and H. Schmidt, *Solid State Phenom.* **205–206**, 151 (2014).

⁶S. Schneider, H. Bracht, J. N. Klug, J. Lundgaard-Hansen, A. Nylandsted-Larsen, D. Bougeard, and E. E. Haller, *Phys. Rev. B* **87**, 115202 (2013).

⁷N. E. B. Cowern, G. F. A van de Walle, D. J. Gravesteijn, and C. J. Vriezema, *Phys. Rev. Lett.* **67**, 212 (1991).

⁸E. Bruno, S. Mirabella, G. Scapellato, G. Impellizzeri, A. Terrasi, F. Priolo, E. Napolitani, D. De Salvador, M. Mastromatteo, and A. Camera, *Phys. Rev. B* **80**, 033204 (2009).

⁹N. E. B. Cowern, K. T. F. Janssen, G. F. A. van de Walle, and D. J. Gravesteijn, *Phys. Rev. Lett.* **65**, 2434 (1990).

¹⁰N. E. B. Cowern, B. Colombeau, F. Roozeboom, M. Hopstaken, H. Snijders, P. Meunier-Beillard, and W. Lerch, in *Si Front-End Formation Technologies*, edited by D. F. Downey, M. E. Law, A. P. Claverie, and M. J. Rendon (Mater. Res. Soc. Symp. Proc., 2002), Vol. 717, p. 255.

¹¹S. Uppal, A. F. W. Willoughby, J. M. Bonar, N. E. B. Cowern, T. Grasby, R. J. H. Morris, and M. G. Dowsett, *J. Appl. Phys.* **96**, 1376 (2004).

¹²The beam flux in Ref. 8 is $0.37\times$ that in Ref. 1, but the number of FPs produced per proton is about $3\times$ higher.

¹³The doping-independence of λ at 550°C confirms that, at least at this temperature, the reaction $B_s + I \leftrightarrow BI$ is charge balanced without the involvement of charge carriers.

¹⁴G. G. Scapellato, E. Bruno, A. J. Smith, W. Napolitani, D. De Salvador, S. Mirabella, M. Mastromatteo, A. Camera, R. Gwilliam, and F. Priolo, *Nucl. Instrum. Methods Phys. Res. B* **282**, 8 (2012).

¹⁵The data point at $\lambda = 1.5\text{ nm}$ in Fig. 2 of Ref. 2 is superseded by one with threefold improved accuracy,¹⁴ shown here.

¹⁶H. Haesslein, R. Sielemann, and C. Zistl, *Phys. Rev. Lett.* **80**, 2626 (1998).

¹⁷R. Sielemann, *Nucl. Instrum. Methods Phys. Res. B* **146**, 329 (1998).

¹⁸P. Śpiewak, J. Vanhellefont, K. Sueoka, K. J. Kurzydowski, and I. Romandic, *Mater. Sci. Semicond. Proc.* **11**, 328 (2008).

¹⁹D. Alloyeau, B. Freitag, S. Dag, L. W. Wang, and C. Kisielowski, *Phys. Rev. B* **80**, 014114 (2009).

²⁰S. Simdyankin and J. P. Goss, private communication (2013).